NPN Silicon Power Transistor

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- High Gain
- Low Saturation Voltage
- High Current Gain Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	45	Vdc
Collector-Base Voltage	V _{CB}	45	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	I _C	4.0	Adc
Collector Current – Peak	I _{CM}	7.0	Adc
Base Current	I _B	50	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

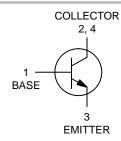
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

www.onsemi.com

POWER TRANSISTOR 4.0 AMPERES 45 VOLTS, 20 WATTS





DPAK CASE 369C STYLE 1

MARKING DIAGRAM



= Assembly Location

= Year WW = Work Week J148 = Device Code = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJD148T4G	DPAK (Pb-Free)	2,500/Tape & Reel
NJVMJD148T4G	DPAK (Pb-Free)	2,500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$, unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 100 mAdc, I _B = 0)	V _{CEO(sus)}	45	_	Vdc
Collector Cutoff Current (V _{CB} = 45 Vdc, I _E = 0)	I _{CBO}	-	20	μAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	1	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 0.5 \text{ Adc}$, $V_{CE} = 1 \text{ Vdc}$) ($I_C = 2 \text{ Adc}$, $V_{CE} = 1 \text{ Vdc}$) ($I_C = 3 \text{ Adc}$, $V_{CE} = 1 \text{ Vdc}$)	h _{FE}	40 85 50 30	- 375 - -	-
Collector–Emitter Saturation Voltage ($I_C = 2$ Adc, $I_B = 0.2$ Adc)	V _{CE(sat)}	-	0.5	Vdc
Base–Emitter On Voltage (I _C = 2 Adc, V _{CE} = 1 Vdc)	V _{BE(on)}	-	1.1	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain–Bandwidth Product (I _C = 250 mAdc, V _{CE} = 1 Vdc, f = 1 MHz)	f _T	3	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

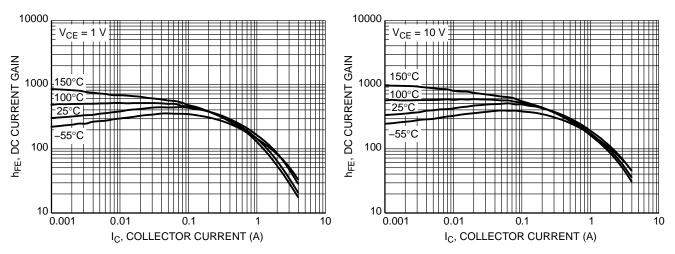


Figure 1. DC Current Gain

Figure 2. DC Current Gain

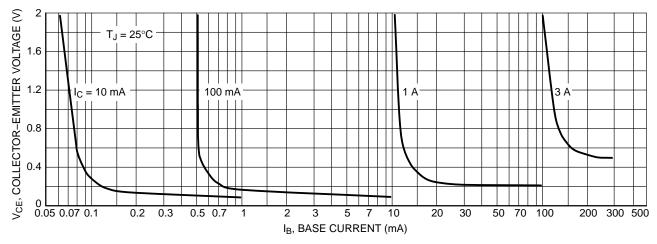


Figure 3. Collector Saturation Region

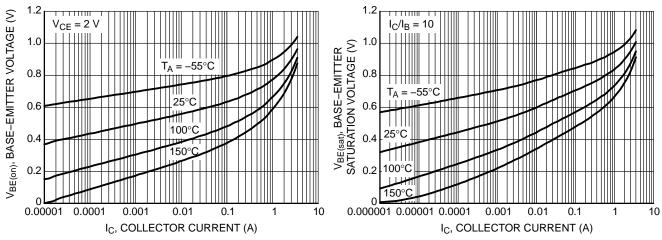


Figure 4. Base Emitter Voltage vs. Collector Current

Figure 5. Base Emitter Saturation Voltage vs.
Collector Current

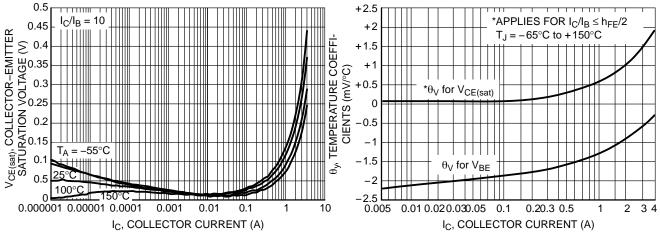


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

Figure 7. Temperature Coefficients

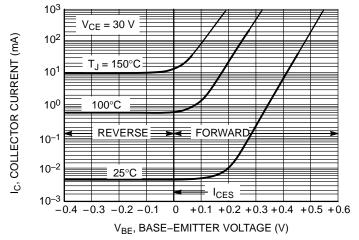


Figure 8. Collector Cut-Off Region

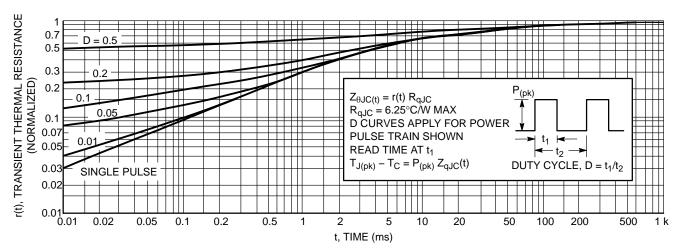


Figure 9. Thermal Response

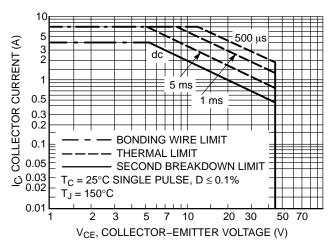


Figure 10. Maximum Rated Forward Bias

Forward Bias Safe Operating Area Information

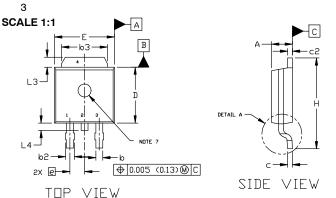
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 10 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 9. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

DPAK (SINGLE GAUGE)

CASE 369C ISSUE G

DATE 31 MAY 2023

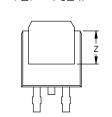


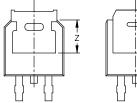


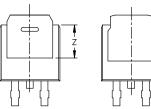
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE DUTERMOST EXTREMES OF THE PLASTIC BODY.

 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
b	0.025	0.035	0.63	0.89	
b2	0.028	0.045	0.72	1.14	
b3	0.180	0.215	4.57	5.46	
С	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
E	0.250	0.265	6.35	6.73	
е	0.090	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.114 REF		2.90	REF	
L2	0.020 BSC		0.51	BSC	
L3	0.035	0.050	0.89	1.27	
L4		0.040		1.01	
Z	0.155		3.93		





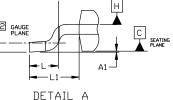


BOTTOM VIEW

5.80

BOTTOM VIEW ALTERNATE

CONSTRUCTIONS [0.228] 6.20 L2 GAUGE PLANE [0.244] 2.58 3.00 [0.102] [0.118] 1.60 [0.063] 6.17



STYLE 5: PIN 1. GATE

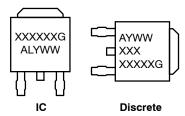
2. ANODE

3 CATHODE

ANODE

CW ROTATED 90°

GENERIC MARKING DIAGRAM*



= Device Code
= Assembly Location
= Wafer Lot
= Year
= Work Week
= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT* *FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

[0.243]

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. GATE STYLE 3: PIN 1. ANODE STYLE 4: PIN 1. CATHODE 2. COLLECTOR 2. DRAIN 2. CATHODE 2. ANODE 3 SOURCE 3 FMITTER 3 ANODE 3 GATE

COLLECTOR 4. DRAIN 4. CATHODE 4. ANODE STYLE 6: STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 8: STYLE 9: PIN 1. MT1 2. MT2

STYLE 10: PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE PIN 1. CATHODE 2. ANODE 3 CATHODE 3 FMITTER 3 RESISTOR ADJUST 4. COLLECTOR 4. CATHODE 4. ANODE CATHODE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

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3 GATE

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